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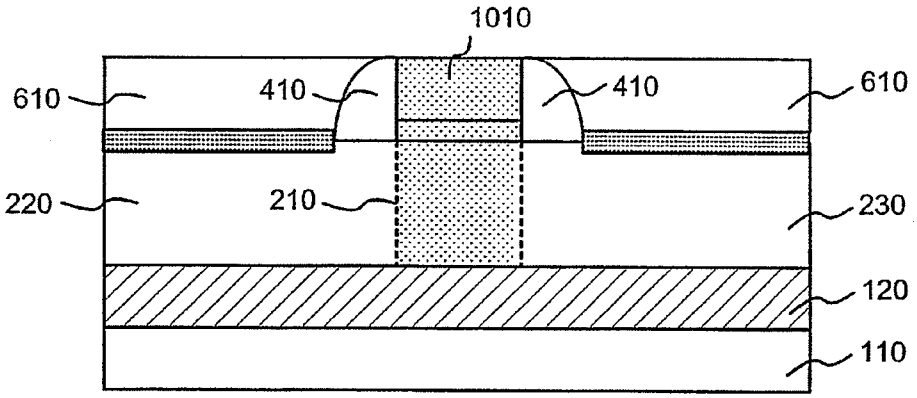
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(54) Title: METHOD FOR FORMING A GATE IN A FINFET DEVICE AND THINNING A FIN IN A CHANNEL REGION OF THE FINFET DEVICE

100



(57) Abstract: A method of manufacturing a FinFET device (100) includes forming a fin structure (210) on an insulating layer (120). The fin structure (210) includes a conductive fin. The method also includes forming source/drain regions (220/230) and forming a dummy gate (300) over the fin (210). The dummy gate (300) may be removed and the width of the fin (210) in the channel region may be reduced. The method further includes depositing a gate material (1010) to replace the removed dummy gate (300).

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